The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

- 1. (Canceled)
- (Currently Amended) A film-like article comprising:

a substrate having a groove:

a thin film integrated circuit capable of storing information described on the filmlike-article substrate; and

an antenna in the groove, the antenna being connected to the thin film integrated circuit. [[.1]

wherein the thin film integrated circuit is mounted inside the film like article. wherein the antenna is mounted on a surface of the film-like article, and wherein the antenna is electrically connected to the thin film integrated circuit through an opening of the film-like article.

- 3. (Canceled)
- 4. (Currently Amended) A film-like article according to Claim 2,

wherein when a thickness of the film-like article is D, a position to dispose the thin film integrated circuit X may be set so as to satisfy (1/2)·D - 30 µm < X < (1/2)·D + 30 um.

5. (Previously Presented) A film-like article comprising: a IDF chip:

an antenna connected to the IDF chip through an anisotropic conductor; and a resin covering the IDF chip and the antenna,

wherein the IDF chip and the antenna are provided in a depression of the filmlike article.

(Currently Amended) A film-like article comprising:

a substrate;

a thin-film-integrated circuit capable of storing information described on the substrate film-like article; and

a first [[an]] antenna on a top surface of the substrate; and connected to the thin film integrated circuit,

a second antenna on a bottom surface of the substrate,

wherein the first antenna is electrically connected to the second antenna through an opening of the substrate, and

wherein the first antenna and the second antenna are electrically connected to the circuit.

wherein the thin film integrated circuit is mounted on a surface of the film-like article.

wherein the antenna is mounted inside the film like article, and

wherein-the-antenna-is-electrically-connected-to-the-thin-film-integrated-circuit through an opening of the film-like article.

7.-13. (Canceled)

- (Currently Amended) A film-like article according Claim 2,
 wherein the thin film-integrated circuit has light-transmitting characteristic.
- 15. (Currently Amended) A film-like article according Claim 5,

wherein the thin film integrated circuit IDF chip has light-transmitting characteristic

- 16. (Currently Amended) A film-like article according Claim 6, wherein the thin film integrated circuit has light-transmitting characteristic.
- 17.-18. (Canceled)
- 19. (Currently Amended) A film-like article according to Claim 2. wherein the thin film integrated circuit has an insulating film containing nitrogen.
- 20. (Currently Amended) A film-like article according to Claim 5, wherein the thin film integrated circuit IDF chip has an insulating film containing nitrogen.
 - (Currently Amended) A film-like article according to Claim 6. wherein the thin film integrated circuit has an insulating film containing nitrogen.
 - 22.-23. (Canceled)
- 24. (Currently Amended) A film-like article according to Claim 2. wherein thickness of the thin film integrated circuit is in a range of 0.1 µm to 3 um.
- 25. (Currently Amended) A film-like article according to Claim 5. wherein thickness of the thin film integrated circuit IDF chip is in a range of 0.1 µm to 3 µm.

 (Currently Amended) A film-like article according to Claim 6, wherein thickness of the thin-film integrated circuit is in a range of 0.1 μm to 3 μm.

27.-28. (Canceled)

- 29. (Currently Amended) A film-like article according to Claim 2, wherein the thin film integrated circuit has a semiconductor film containing hydrogen of 1 x 10¹⁹ atoms/cm³ to 5 x 10²⁰ atoms/cm³.
- 30. (Currently Amended) A film-like article according to Claim 5, wherein the thin film integrated circuit IDF chip has a semiconductor film containing hydrogen of 1 x 10¹⁹ atoms/cm³ to 5 x 10²⁰ atoms/cm³.
- 31. (Currently Amended) A film-like article according to Claim 6, wherein the thin-film integrated circuit has a semiconductor film containing hydrogen of 1 x 10¹⁹ atoms/cm³ to 5 x 10²⁰ atoms/cm³.
 - 32. (Canceled)
- 33. (Previously Presented) A film-like article according to any one of Claims 29 to 31,

wherein the semiconductor film includes a source, a drain, and a channel region, and

the source, the drain, and the channel region are provided perpendicular to direction of bending the film-like article.

34. (Canceled)

 (Currently Amended) A film-like article according to Claim 2, wherein the film-like article comprises a plurality of thin film-integrated circuits, and

the plurality of thin film integrated circuits are integrated with antennas.

 (Currently Amended) A film-like article according to Claim 5, wherein the film-like article comprises a plurality of thin film-integrated circuits IDF chips, and

the plurality of thin film integrated circuits IDF chips are integrated with antennas.

 (Currently Amended) A film-like article according to Claim 6, wherein the film-like article comprises a plurality of thin film integrated circuits, and

the plurality of thin film integrated circuits are integrated with antennas.

- 38.-39. (Canceled)
- 40. (Original) A film-like article according to Claim 2, wherein the film-like article is a business card.
- 41. (Original) A film-like article according to Claim 5, wherein the film-like article is a business card.
- 42. (Original) A film-like article according to Claim 6, wherein the film-like article is a business card.
- 43.-48. (Canceled)